Search Text DB Hits Number 2003/03/01 USPAT; micron.as. and circuitry and capacitor 1788 12:04 US-PGPUB; EPO; JPO; DERWENT; IBM TDB 2003/03/01 (micron.as. and circuitry and capacitor) USPAT; 56 12:03 US-PGPUB; and crystalline and amorphous EPO; JPO; DERWENT; IBM TDB micron.as. and capacitor and crystalline USPAT; 2003/03/01 169 and amorphous US-PGPUB; 12:04 EPO; JPO; DERWENT; IBM TDB 2003/03/01 (micron.as. and capacitor and crystalline USPAT: US-PGPUB; 12:11 and amorphous) not ((micron.as. and circuitry and capacitor) and crystalline EPO; JPO; DERWENT; and amorphous) IBM TDB dielectric with amorphous and dielectric 2003/03/01 USPAT; 285 12:13 US-PGPUB; with crystalline and capacitor EPO; JPO; DERWENT; IBM TDB 2003/03/01 USPAT; jp-01315124-\$.did. US-PGPUB; 13:47 EPO; JPO; DERWENT; IBM TDB 2003/03/01 stack adj capacitor with parallel adj USPAT; 0 US-PGPUB; 13:48 plate adj capacitor EPO; JPO; DERWENT; IBM TDB 2003/03/01 USPAT; stacked adj capacitor with parallel adj 0 US-PGPUB; 13:50 plate adj capacitor EPO; JPO; DERWENT; IBM TDB 2003/03/01 USPAT; 509 (257/303).CCLS. US-PGPUB; 13:51 EPO; JPO; DERWENT; IBM TDB 2003/03/01 USPAT; 136 ((257/303).CCLS.) and parallel 13:51 US-PGPUB; EPO; JPO; DERWENT; IBM TDB 2003/03/01 USPAT; ((257/303).CCLS.) and parallel with 90 (plate electrode capacitor) US-PGPUB; 13:53 EPO; JPO; DERWENT; IBM TDB 2003/03/01 stacked with capacitor and parallel with USPAT; 1565 13:54 US-PGPUB: (plate electrode capacitor) EPO; JPO; DERWENT; IBM TDB stacked with capacitor and parallel adj USPAT; 2003/03/01 326 13:55 (plate electrode capacitor) US-PGPUB; EPO; JPO; DERWENT; IBM TDB

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_	61	"5150276"	USPAT;	2003/03/01
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